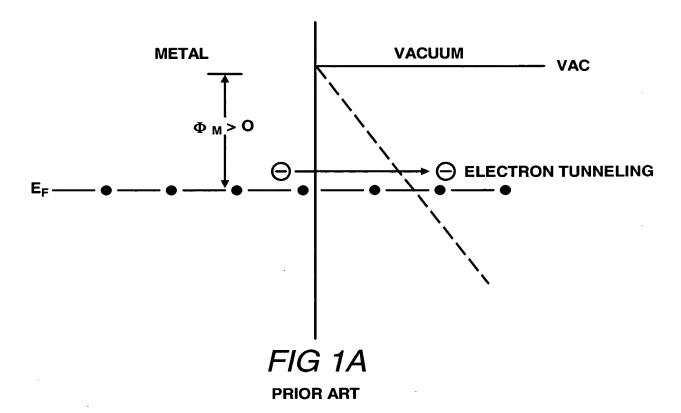
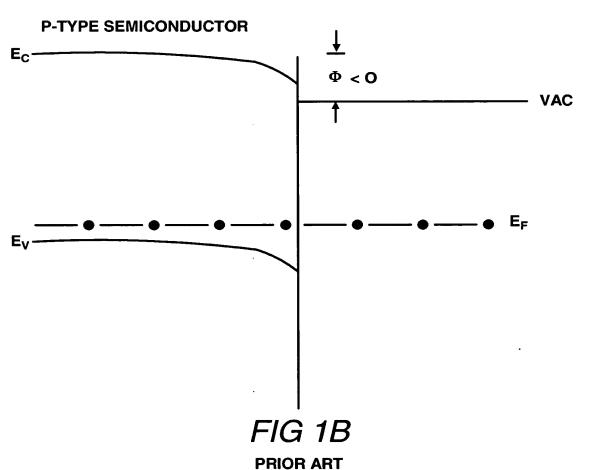


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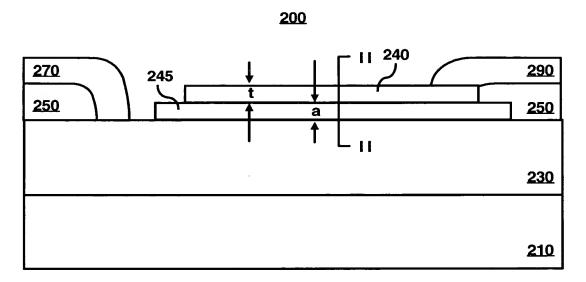


FIG 2A

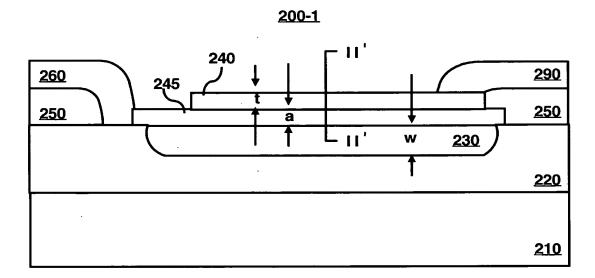


FIG 2B



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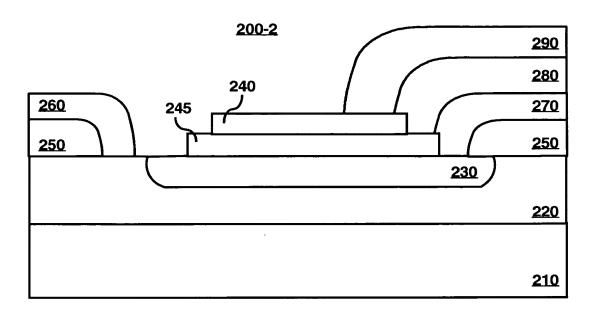
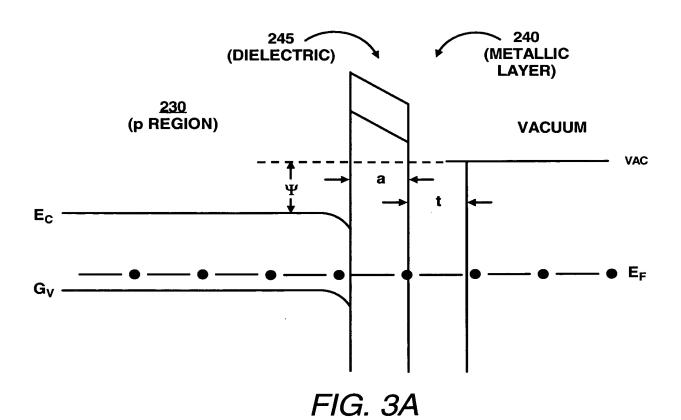


FIG 2C



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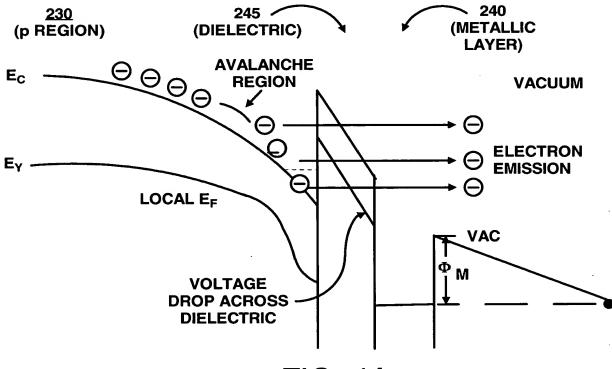


FIG. 4A



High-Current Avalanche-Tunneling And Injection-Tunneling Semiconductor-Dielectric-Metal Stable Cold Emitter . . . Viatcheslav V. OSSIPOV et al. Docket No. 10017286-1



